L Number	Hits	Search Text	DB	Trimo ata
1	4		USPAT;	Time stamp 2004/08/24 11:26
2		or 6572705.pn.	US-PGPUB	2004/00/24 11.20
2	2		USPAT;	2004/08/24 13:01
	}	and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5	US-PGPUB;	
		or regulat\$3 or optimiz\$5 or monitor\$3)	EPO; JPO;	
		near5 (wall or chamber or reactor) near5	DERWENT; IBM TDB	
1_	i	temperature))	IDM_IDB	
3	34	1 (DOINGE OF DEMOCROTOR TILL OF DOINGES CAME III.)	USPAT;	2004/08/24 11:29
	ļ	and ((ALE or ALD or (atomic adj layer adj	US-PGPUB;	
		(deposit\$3 or epitax\$5))) and (substrate near5 temperature) and ((wall or reactor	EPO; JPO;	
1		or chamber) near5 temperature))	DERWENT;	
4	2	(ASM.as. or Lindfors.in, or Bondestam.in.)	IBM_TDB USPAT;	2004/08/24 13:06
]		and ((ALE or ALD or (atomic adi laver adi	US-PGPUB;	2004/00/24 13:06
1		(deposit\$3 or epitax\$5))) and ((substrate	EPO; JPO;	
		near5 temperature) with (differ\$4 or	DERWENT;	
]		increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or	IBM_TDB	
		reactor or chamber) near5 temperature)))		
5	12	(ASM.as. or Lindfors.in. or Bondestam.in.)	USPAT;	2004/08/24 13:10
		and ((ALE or ALD or (atomic adi laver adi	US-PGPUB;	
		(deposit\$3 or epitax\$5))) with wall)	EPO; JPO;	
			DERWENT;	
6	20	(ASM.as. or Lindfors.in. or Bondestam.in.)	IBM_TDB USPAT:	0004/00/01 15
		and ((ALE or ALD or (atomic adi laver adi	US-PGPUB;	2004/08/24 12:33
1		(deposit\$3 or epitax\$5))) with rate with	EPO; JPO;	
1		reduc\$5 or low\$5 or adjust\$5 or minimiz\$6	DERWENT;	
7	3122	or control\$5))	IBM_TDB	ļ
	3122	(427/248.1,255.23,255.28,255.7).CCLs.	USPAT;	2004/08/24 12:33
8	278	(427/487).CCLS.	US-PGPUB USPAT;	2004/00/04 40 00
			US-PGPUB	2004/08/24 12:33
9	5960	(118/715,719,724,725,728).CCLS.	USPAT;	2004/08/24 12:34
10	1414	(117/04 05 00 105 000 001)	US-PGPUB	
	1414	(117/84,85,88,105,200,201).CCLS.	USPAT;	2004/08/24 12:34
11	10149	((427/248.1,255.23,255.28,255.7).CCLS.)	US-PGPUB	2004/00/04 40 81
] }		((427/487).CCLS.)	USPAT; US-PGPUB	2004/08/24 12:34
	Ī	((118/715,719,724,725,728).CCLS.)	oo rarab	
12	11	((117/84,85,88,105,200,201).CCLS.)		
1	11	(((427/248.1,255.23,255.28,255.7).CCLs.) ((427/487).CCLs.)	USPAT;	2004/08/24 13:21
		((118/715,719,724,725,728).CCLS.)	US-PGPUB	
]	1	((117/84,85,88,105,200,201).CCLS.)) and	i	
		((ALE or ALD or (atomic adi laver adi		
13	16	(deposit\$3 or epitax\$6))) near4 wall)		
	Το	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.)	USPAT;	2004/08/24 13:10
		((118/715,719,724,725,728).CCLS.)	US-PGPUB	
		((117/84,85,88,105,200,201).CCLS.)) and	ŀ	
	Ì	((ALE or ALD or (atomic adj laver adj	ļ	
14	24	(deposit\$3 or epitax\$6))) near6 wall)		
	34	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.)	USPAT;	2004/08/24 12:43
]	1	((118/715,719,724,725,728).CCLS.)	US-PGPUB	
	1	((117/84,85,88,105,200,201),CCLS.)) and		
†	ļ	(ALE or ALD or (atomic adj laver adj		
1		(deposit\$3 or epitax\$6))) and ((heat\$3 or	1	
		temperature) near3 wall) and ((heat\$3 or	1	
	}	temperature) near3 (support or susceptor or substrate or base or wafer))	ļ	

15	71	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.)	USPAT; US-PGPUB	2004/08/24 13:25
		((118/715,719,724,725,728).CCLS.)	OS FGFOB	
		((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj		
		(deposit\$3 or epitax\$6))) and ((deposit\$3		
	1	or decompos\$5 or condens\$5 or contaminat\$4		
		or coat\$3) near3 (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5) with (chamber or		
		vessel or reactor or wall))		
16	18		USPAT;	2004/08/24 13:02
		((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.)	US-PGPUB;	
		((117/84,85,88,105,200,201).CCLS.)) and	EPO; JPO; DERWENT;	
		((ALE or ALD or (atomic adj layer adj	IBM_TDB	
		<pre>(deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3)</pre>		
		near5 (wall or chamber or reactor) near5		
17	17	temperature))		
17	17	((((427/248.1,255.23,255.28,255.7).CCLS.)	USPAT;	2004/08/24 13:02
		((118/715,719,724,725,728).CCLS.)	US-PGPUB; EPO; JPO;	
		((117/84,85,88,105,200,201).CCLS.)) and	DERWENT;	
		((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5	IBM_TDB	
		or regulat\$3 or optimiz\$5 or monitor\$3)		
i		near5 (wall or chamber or reactor) near5		
		temperature))) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE		
		or ALD or (atomic adj layer adj (deposit\$3		
		or epitax\$5))) same ((control\$5 or		
		regulat\$3 or optimiz\$5 or monitor\$3) near5 (wall or chamber or reactor) near5		
1.0		temperature)))		
18	20	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.)	USPAT;	2004/08/24 13:03
		((118/715,719,724,725,728).CCLS.)	US-PGPUB; EPO; JPO;	
		((117/84,85,88,105,200,201).CCLS.)) and	DERWENT;	,
		((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5	IBM_TDB	
	1	or regulat\$3 or optimiz\$5 or monitor\$3 or	ĺ	
	1	adjust\$4) near5 (wall or chamber or		
19	19	reactor) near5 temperature)) ((((427/248.1,255.23,255.28,255.7).CCLS.)	USPAT;	2004/08/24 13:03
	ĺ	((427/487).CCLS.)	US-PGPUB;	2004/06/24 13:03
		((118/715,719,724,725,728).CCLS.)	EPO; JPO;	
]	((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj	DERWENT; IBM_TDB	
		(deposit\$3 or epitax\$5))) same ((control\$5	100	
		or regulat\$3 or optimiz\$5 or monitor\$3 or adjust\$4) near5 (wall or chamber or		
		reactor) near5 temperature))) not		
		((ASM.as. or Lindfors.in. or		
		Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5)))		
		same ((control\$5 or regulat\$3 or optimiz\$5		
	ĺ	or monitor\$3) near5 (wall or chamber or	II.	
20	9	reactor) near5 temperature))) (((427/248.1,255.23,255.28,255.7).CCLS.)	IIQDAT.	2004/00/04 12 25
	-	((427/487).CCLS.)	USPAT; US-PGPUB;	2004/08/24 13:06
		((118/715,719,724,725,728).CCLS.)	EPO; JPO;	
] -	((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj	DERWENT; IBM TDB	
		(deposit\$3 or epitax\$5))) and ((substrate	1211_100	
		near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower		
]	or greater or lesser) with ((wall or		
		reactor or chamber) near5 temperature)))		

[01			· • · · · · · · · · · · · · · · · · · ·	
21	11	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/08/24 13:36
		((427/487).CCLS.)	US-PGPUB;	
		((118/715,719,724,725,728).CCLS.)	EPO; JPO;	
		((117/84,85,88,105,200,201).CCLS.)) and	DERWENT;	
		((ALE or ALD or (atomic adj layer adj	IBM TDB	
		(deposit\$3 or epitax\$5))) and (((substrate	12011_100	
	1			
	1	or support or pedestal or wafer) near5		
		temperature) with (differ\$4 or increas\$3		
		or decreas\$3 or higher or lower or greater		
		or lesser) with ((wall or reactor or		
		chamber) near5 temperature)))		
22	10		USPAT;	2004/08/24 13:07
		((427/487).CCLS.)	1	2004/00/24 13:07
			US-PGPUB;	
		((118/715,719,724,725,728).CCLS.)	EPO; JPO;	
		((117/84,85,88,105,200,201).CCLS.)) and	DERWENT;	
		((ALE or ALD or (atomic adj layer adj	IBM TDB	
		(deposit\$3 or epitax\$5))) and (((substrate	_	
		or support or pedestal or wafer) near5		
		temperature) with (differ\$4 or increas\$3		
		or decreas\$3 or higher or lower or greater		
		or lesser) with ((wall or reactor or		
		chamber) near5 temperature)))) not		
]		((ASM.as. or Lindfors.in. or		
1		Bondestam.in.) and ((ALE or ALD or (atomic		1
		adj layer adj (deposit\$3 or epitax\$5)))		
		and ((substrate near5 temperature) with		
		(differ\$4 or increas\$3 or decreas\$3 or		
		higher or lower or greater an learny with		
		higher or lower or greater or lesser) with		
		((wall or reactor or chamber) near5		1
		temperature))))		
23	6	(((427/248.1,255.23,255.28,255.7).CCLS.)	USPAT;	2004/08/24 13:17
		((427/487).CCLS.)	US-PGPUB	,
İ	ļ	((118/715,719,724,725,728).CCLS.)		
	1	((117/84,85,88,105,200,201).CCLS.)) and		
		((ALE or ALD or (atomic adj layer adj		
		(ALE OF ALL OF (acoustic adj layer adj		ļ
		(deposit\$3 or epitax\$6))) with (wall or		
		reactor or chamber) with (reduc\$5 or		l
		minimiz\$6 or lower or low\$3 or prevent\$5		
		or eliminat\$6) with rate)		
24	57	(((427/248.1,255.23,255.28,255.7).CCLS.)	USPAT;	2004/08/24 13:13
1		((427/487).CCLS.)	US-PGPUB	2004/00/24 13:13
		((118/715,719,724,725,728).CCLS.)	OB-FGFOB	
	İ	((110/713,719,724,723,720).CCLS.)		
		((117/84,85,88,105,200,201).CCLS.)) and		
	1	((ALE or ALD or (atomic adj layer adj		
1	1	(deposit\$3 or epitax\$6))) with (wall or		
	1	reactor or chamber) with (reduc\$5 or		
		minimiz\$6 or lower or low\$3 or prevent\$5		
		or eliminat\$6))		
25	51	((((427/248.1,255.23,255.28,255.7).CCLS.)	HIGDAT.	2004/09/24 12:12
		((427/487).CCLS.)	USPAT;	2004/08/24 13:13
	[US-PGPUB	
		((118/715,719,724,725,728).CCLS.)		
		((117/84,85,88,105,200,201).CCLS.)) and		1
		((ALE or ALD or (atomic adj layer adj		
		(deposit\$3 or epitax\$6))) with (wall or		İ
1		reactor or chamber) with (reduc\$5 or		
		minimiz\$6 or lower or low\$3 or prevent\$5		
		or eliminat\$6))) not		
		((((427/248.1,255.23,255.28,255.7).CCLS.)		
		((427/487).CCLS.)		
1		((118/715,719,724,725,728).CCLS.)		
		((117/84,85,88,105,200,201).CCLS.)) and		,
		((ALE or ALD or (atomic adj layer adj		'
		(deposit\$3 or epitax\$6))) with (wall or		1
		(deposit\$3 or epitax\$6))) with (wall or	:	Ì
		(deposit\$3 or epitax\$6))) with (wall or reactor or chamber) with (reduc\$5 or	į	
		(deposit\$3 or epitax\$6))) with (wall or	;	

26	11	1 (((=	USPAT;	2004/08/24 13:18
		((427/487).CCLS.)	US-PGPUB	
		((118/715,719,724,725,728).CCLS.)		
		((117/84,85,88,105,200,201).CCLS.)) and		
		((ALE or ALD or (atomic adj layer adj		
	1	(deposit\$3 or epitax\$6))) with (wall or		
		reactor or chamber) with (rate near4 (ALE or ALD or deposit\$3 or grow\$4)))		}
27	37			
1 - '	1 3'	(deposit\$3 or epitax\$6))) near4 wall)	USPAT;	2004/08/24 13:21
28	26		US-PGPUB	2004/00/04 45 54
1		(deposit\$3 or epitax\$6))) near4 wall))	USPAT; US-PGPUB	2004/08/24 13:21
		not	US-PGPUB	
İ	i	((((427/248.1,255.23,255.28,255.7).CCLS.)		}
ļ		((427/487).CCLS.)		1
	Ì	((118/715,719,724,725,728).CCLS.)		1
ļ		((117/84,85,88,105,200,201).CCLS.)) and	1	
		((ALE or ALD or (atomic adj layer adj		1
		(deposit\$3 or epitax\$6))) near4 wall))		
29	36	1 (time of table of table ad tayer ad	USPAT;	2004/08/24 13:24
		(deposit\$3 or epitax\$6))) same ((deposit\$3	US-PGPUB	
		or decompos\$5 or condens\$5 or contaminat\$4		1
		or coat\$3 or grow\$4) near3 (minimiz\$5 or	1	
1		eliminat\$3 or prevent\$3 or avoid\$5 or		
		reduc\$6 or low\$4) with (chamber or vessel or reactor or wall) with (hot or cold or		
		temperature or heat\$3 or cool\$3)))		1
30	27	(((ALE or ALD or (atomic adj layer adj	HCDAM.	2004/00/04 15 25
	1	(deposit\$3 or epitax\$6))) same ((deposit\$3	USPAT; US-PGPUB	2004/08/24 13:25
		or decompos\$5 or condens\$5 or contaminat\$4	US-FGFUB	
		or coat\$3 or grow\$4) near3 (minimiz\$5 or		
		eliminat\$3 or prevent\$3 or avoid\$5 or		· I
	ľ	reduc\$6 or low\$4) with (chamber or vessel		1
		or reactor or wall) with (hot or cold or		1
		temperature or heat\$3 or cool\$3)))) not		
		((((427/248.1,255.23,255.28,255.7).CCLS.)		i
		((427/487).CCLS.)		1
		((118/715,719,724,725,728).CCLS.)		,
	İ	((117/84,85,88,105,200,201).CCLS.)) and	ļ	
1		(ALE or ALD or (atomic adj layer adj		
		<pre>(deposit\$3 or epitax\$6))) and ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4</pre>		1
ł		or coat\$3) near3 (minimiz\$5 or eliminat\$3		
	1	or prevent\$3 or avoid\$5) with (chamber or	ļ	j
		vessel or reactor or wall)))		
31	25	((ALE or ALD or (atomic adj layer adj	USPAT;	2004/08/24 13:28
	İ	(deposit\$3 or epitax\$6))) same ((deposit\$3	US-PGPUB	2004/08/24 13:28
		or decompos\$5 or condens\$5 or contaminat\$4	10100	
		or coat\$3 or grow\$4) with (wall) with (hot		
		or cold or temperature or heat\$3 or		
32	10	((/ALE - ALE		
32	10	I ((o o - (acomic au l'aver au l'	USPAT;	2004/08/24 13:28
		(deposit\$3 or epitax\$6))) same ((deposit\$3	US-PGPUB	
		or decompos\$5 or condens\$5 or contaminat\$4		
1		or coat\$3 or grow\$4) with (wall) with (hot or cold or temperature or heat\$3 or		
		cool\$3)))) not (((ALE or ALD or (atomic		}
İ		adj layer adj (deposit\$3 or epitax\$6)))		
1	}	same ((deposit\$3 or decompos\$5 or		
		condens\$5 or contaminat\$4 or coat\$3 or		
	[grow\$4) near3 (minimiz\$5 or eliminat\$3 or		
		prevent\$3 or avoid\$5 or reduc\$6 or low\$4)		
	ļĺ	with (chamber or vessel or reactor or		
		wall) with (hot or cold or temperature or		
33	1 11	neat\$3 or cool\$3))))		
ا	11	((ALE or ALD or (atomic adj layer adj	USPAT;	2004/08/24 13:31
	[(deposit\$3 or epitax\$6))) and ((wall with	US-PGPUB	
	ļ	(substrate or support or base or susceptor		
		or wafer) with (higher or lower or different or difference or greater or		
		lesser or increas\$4 or decreas\$4) with		
	1	(temperature))))		
Search His		24/04 1:39:39 PM		

34	0	(/ATE on ATD (+ · · · · · · · · · · · · · · · · · ·		
1 .	1	(\table of the of (acomic ad) taver and	EPO; JPO;	2004/08/24 13:32
		(deposit\$3 or epitax\$6))) and ((wall with	DERWENT;	1
		(substrate or support or base or susceptor	IBM_TDB	
1	ļ	or wafer) with (higher or lower or		
ł		different or difference) with		
35	14	(temperature))))		
	14	I (or ripp or (acourte ad lavel ad)	EPO; JPO;	2004/08/24 13:33
		(deposit\$3 or epitax\$6))) with (DERWENT;	
l		(minimiz\$5 or eliminat\$3 or prevent\$3 or	IBM_TDB	
	i	avoid\$5) with (chamber or vessel or]	1
36	2	reactor or wall)))		
1 30		I the or the or tacomic autifacer and	EPO; JPO;	2004/08/24 13:34
1	1	(deposit\$3 or epitax\$6))) with (DERWENT;	
	Ì	(minimiz\$5 or eliminat\$3 or prevent\$3 or	IBM_TDB	1
		avoid\$5) with (chamber or vessel or		
		reactor or wall) with (hot or cold or		1
37	1	temperature or heat\$3 or cool\$3)))		ļ
"	_	((ALE or ALD or (atomic adj layer adj	EPO; JPO;	2004/08/24 13:35
]		(deposit\$3 or epitax\$6))) same ((deposit\$3	DERWENT;	
		or decompos\$5 or condens\$5 or contaminat\$4	IBM_TDB	1
i		or coat\$3) with (wall) with (hot or cold		
38	6	or temperature or heat\$3 or cool\$3)))]
]	١	((ALE or ALD or (atomic adj layer adj	EPO; JPO;	2004/08/24 13:35
Ì	ł	(deposit\$3 or epitax\$6))) near4 wall)	DERWENT;	1
39	0	((ALE or ALD or (atomic and law)	IBM_TDB	1
	Ĭ	((ALE or ALD or (atomic adj layer adj	EPO; JPO;	2004/08/24 13:37
1		(deposit\$3 or epitax\$5))) and (((substrate or support or pedestal or wafer) near5	DERWENT;	
]		temperature) with (differ\$4 or increas\$3	IBM_TDB	
		or decreas\$3 or higher or lower or greater		,
}		or lesser) with ((wall or reactor or		
]		chamber) near5 temperature)))		ł
40	12	((ALE or ALD or (atomic adj layer adj	[
]	(deposit\$3 or epitax\$5))) and (((substrate)	EPO; JPO;	2004/08/24 13:37
]	or support or pedestal or wafer) near5	DERWENT;	
	Ì	temperature) with ((wall or reactor or	IBM_TDB	
ĺ	ł	chamber) near5 temperature)))		

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